

FAST CMOS 16-BIT BUFFER/LINE DRIVER

IDT54/74FCT162244T/AT/CT/ET

FEATURES:

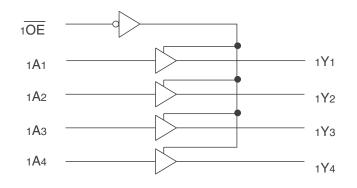
- 0.5 MICRON CMOS Technology
- · High-speed, low-power CMOS replacement for ABT functions
- Typical tsk(o) (Output Skew) < 250ps
- Low input and output leakage $\leq 1\mu A$ (max.)
- ESD > 2000V per MIL-STD-883, Method 3015; > 200V using machine model (C = 200pF, R = 0)
- · Balanced Output Drivers:
 - ±24mA (industrial)
 - ±16mA (military)
- · Reduced system switching noise
- Typical Volp (Output Ground Bounce) < 0.6V at Vcc = 5V, TA = 25°C
- · Available in the following packages:
 - Industrial: SSOP, TSSOP
 - Military: CERPACK

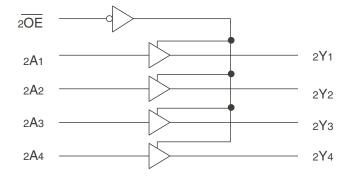
DESCRIPTION:

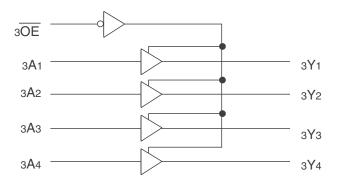
The FCT162244T 16-Bit Buffer/Line Driver is for bus interface or signal buffering applications requiring high speed and low power dissipation. These devices have a flow through pin organization, and shrink packaging to simplify board layout. All inputs are designed with hysteresis for improved noise margin. The three-state controls allow independent 4-bit, 8-bit or combined 16-bit operation. These parts are plug in replacements for 54/74ABT16244 where higher speed, lower noise or lower power dissipation levels are desired.

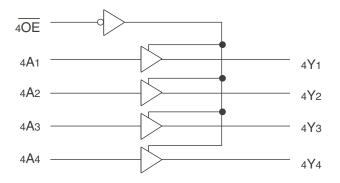
The FCT162244T has balanced output current levels and current limiting resistors. These offer low ground bounce, minimal undershoot, and controlled output fall times, reducing the need for external series terminating resistors while still providing very high speed operation for loads of less than 200pF.

FUNCTIONAL BLOCK DIAGRAM









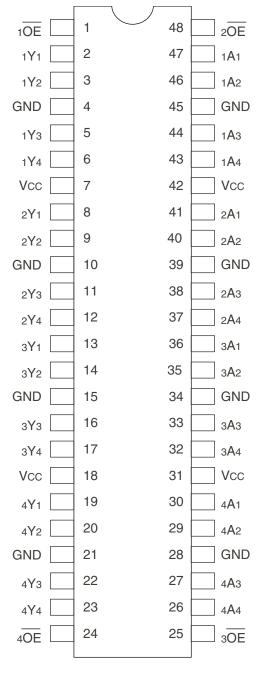
The IDT logo is a registered trademark of Integrated Device Technology, Inc.

MILITARY AND INDUSTRIAL TEMPERATURE RANGES

SEPTEMBER 2009

IDT54/74FCT162244T/AT/CT/ET FASTCMOS16-BITBUFFER/LINEDRIVER

PIN CONFIGURATION



SSOP/ TSSOP/ CERPACK TOP VIEW

MILITARY AND INDUSTRIAL TEMPERATURE RANGES

ABSOLUTE MAXIMUM RATINGS⁽¹⁾

Symbol	Description	Max	Unit
VTERM ⁽²⁾	Terminal Voltage with Respect to GND	–0.5 to +7	V
VTERM ⁽³⁾	Terminal Voltage with Respect to GND	-0.5 to Vcc+0.5	V
Tstg	Storage Temperature	-65 to +150	°C
Ιουτ	DC Output Current	-60 to +120	mA

NOTES:

- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- 2. All device terminals except FCT162XXXT Output and I/O terminals.

3. Output and I/O terminals terminals for FCT162XXXT and FCT166XXXT.

CAPACITANCE (TA = +25°C, F = 1.0MHz)

Syr	mbol	Parameter ⁽¹⁾	Conditions	Тур.	Max.	Unit
CIN	4	Input Capacitance	VIN = 0V	3.5	6	pF
Со	UT	Output Capacitance	Vout = 0V	3.5	8	рF

NOTE:

1. This parameter is measured at characterization but not tested.

PIN DESCRIPTION

Pin Names	Description					
xŌĒ	3-State Output Enable Inputs (Active LOW)					
хАх	Data Inputs					
хҮх	3-State Outputs					

FUNCTION TABLE(1)

Inp	Outputs	
xŌĒ	хАх	хҮх
L	L	L
L	Н	Н
Н	Х	Z

NOTE:

1. H = HIGH Voltage Level

X = Don't Care

L = LOW Voltage Level

Z = High-Impedance

DC ELECTRICAL CHARACTERISTICS OVER OPERATING RANGE

Following Conditions Apply Unless Otherwise Specified:

Industrial: TA = -40°C to +85°C, Vcc = 5.0V ±10%; Military: TA = -55°C to +125°C, Vcc = 5.0V ±10%

Symbol	Parameter	Test Conditions ⁽¹⁾			Тур. ⁽²⁾	Max.	Unit
VIH	Input HIGH Level	Guaranteed Logic HIGH Level		2	_	_	V
VIL	Input LOW Level	Guaranteed Logic LOW Level		_	_	0.8	V
Ін	Input HIGH Current (Input pins) ⁽⁵⁾	Vcc = Max.	VI = VCC	_	_	±1	μA
	Input HIGH Current (I/O pins) ⁽⁵⁾			_	_	±1	
IIL	Input LOW Current (Input pins) ⁽⁵⁾		VI = GND	_	-	±1	
	Input LOW Current (I/O pins) ⁽⁵⁾			_	_	±1	
Іоzн	High Impedance Output Current	Vcc = Max.	Vcc = Max. Vo = 2.7V		_	±1	μA
Iozl	(3-State Output pins) ⁽⁵⁾	Vo = 0.5V		_	_	±1	
νικ	Clamp Diode Voltage	Vcc = Min., IIN = -18mA		_	-0.7	-1.2	V
los	Short Circuit Current	Vcc = Max., Vo = GND ⁽³⁾		-80	-140	-250	mA
Vн	Input Hysteresis	_		_	100	_	mV
ICCL ICCH ICCZ	Quiescent Power Supply Current	Vcc = Max. Vin = GND or Vcc		_	5	500	μA

OUTPUT DRIVE CHARACTERISTICS

Symbol	Parameter	Test Conditions ⁽¹⁾		Min.	Тур.(2)	Max.	Unit
IODL	Output LOW Current	VCC = 5V, VIN = VIH or VIL	., Vo = 1.5V ⁽³⁾	60	115	200	mA
IODH	Output HIGH Current	VCC = 5V, VIN = VIH or VIL, VO = $1.5V^{(3)}$		-60	-115	-200	mA
Vон	Output HIGH Voltage	Vcc = Min	Iон = –16mA MIL	2.4	3.3	_	V
		VIN = VIH or VIL	Iон = –24mA COM'L				
Vol	Output LOW Voltage	Vcc = Min	Ioн = 16mA MIL	_	0.3	0.55	V
		VIN = VIH or VIL	Iон = 24mA COM'L				

NOTES:

1. For conditions shown as Min. or Max., use appropriate value specified under Electrical Characteristics for the applicable device type.

2. Typical values are at Vcc = 5.0V, +25°C ambient.

3. Not more than one output should be shorted at one time. Duration of the test should not exceed one second.

4. Duration of the condition can not exceed one second.

5. This test limit for this parameter is $\pm 5\mu A$ at TA = $-55^{\circ}C$.

POWER SUPPLY CHARACTERISTICS

Symbol	Parameter	Test Conditi	ons ⁽¹⁾	Min.	Тур.(2)	Max.	Unit
Δlcc	Quiescent Power Supply Current TTL Inputs HIGH	Vcc = Max. VIN = 3.4V ⁽³⁾		—	0.5	1.5	mA
ICCD	Dynamic Power Supply Current ⁽⁴⁾	Vcc = Max. Outputs Open xOE = GND One Input Toggling 50% Duty Cycle	Vin = Vcc Vin = GND	_	60	100	μΑ/ MHz
IC	Total Power Supply Current ⁽⁶⁾	Vcc = Max. Outputs Open fi = 10MHz	Vin = Vcc Vin = GND	—	0.6	1.5	mA
		50% Duty Cycle xOE = GND One Bit Toggling	VIN = 3.4V VIN = GND	—	0.9	2.3	
		Vcc = Max. Outputs Open fi = 2.5MHz	VIN = VCC VIN = GND	_	2.4	4.5 ⁽⁵⁾	
		50% Duty Cycle xOE = GND Sixteen Bits Toggling	VIN = 3.4V VIN = GND	_	6.4	16.5 ⁽⁵⁾	

NOTES:

1. For conditions shown as Min. or Max., use appropriate value specified under Electrical Characteristics for the applicable device type.

- 2. Typical values are at Vcc = 5.0V, +25°C ambient.
- 3. Per TTL driven input (VIN = 3.4V). All other inputs at Vcc or GND.
- 4. This parameter is not directly testable, but is derived for use in Total Power Supply Calculations.
- 5. Values for these conditions are examples of the Icc formula. These limits are guaranteed but not tested.
- 6. IC = IQUIESCENT + INPUTS + IDYNAMIC
 - IC = ICC + Δ ICC DHNT + ICCD (fCPNCP/2 + fiNi)
 - Icc = Quiescent Current (IccL, IccH and Iccz)
 - Δ Icc = Power Supply Current for a TTL High Input (VIN = 3.4V)
 - DH = Duty Cycle for TTL Inputs High
 - NT = Number of TTL Inputs at DH
 - ICCD = Dynamic Current caused by an Input Transition Pair (HLH or LHL)
 - fcp = Clock Frequency for Register Devices (Zero for Non-Register Devices)
 - NCP = Number of Clock Inputs at fCP
 - fi = Input Frequency
 - Ni = Number of Inputs at fi

IDT54/74FCT162244T/AT/CT/ET FAST CMOS 16-BIT BUFFER/LINE DRIVER

SWITCHING CHARACTERISTICS OVER OPERATING RANGE

			74FCT1	62244AT	74FCT16	2244CT	74FCT1	62244ET	
Symbol	Parameter	Condition ⁽¹⁾	Min. ⁽²⁾	Max.	Min. ⁽²⁾	Max.	Min. ⁽²⁾	Max.	Unit
tPLH tPHL	Propagation Delay xAx to xYx	CL = 50pF RL = 500Ω	1.5	4.8	1.5	4.1	1.5	3.2	ns
tpzh tpzl	Output Enable Time		1.5	6.2	1.5	5.8	1.5	4.4	ns
tphz tplz	Output Disable Time		1.5	5.6	1.5	5.2	1.5	3.6	ns
tsk(o)	Output Skew ⁽³⁾		—	0.5	—	0.5	—	0.5	ns

			54FCT	162244T	54FCT16	2244AT	54FCT1	62244CT	
Symbol	Parameter	Condition ⁽¹⁾	Min. ⁽²⁾	Max.	Min. ⁽²⁾	Max.	Min. ⁽²⁾	Max.	Unit
tplh tphl	Propagation Delay xAx to xYx	CL = 50pF RL = 500Ω	1.5	7	1.5	5.1	1.5	4.6	ns
tpzh tpzl	Output Enable Time		1.5	8.5	1.5	6.5	1.5	6.5	ns
tPHZ tPLZ	Output Disable Time		1.5	7.5	1.5	5.9	1.5	5.7	ns
tsк(о)	Output Skew ⁽³⁾		—	0.5	—	0.5	_	0.5	ns

NOTES:

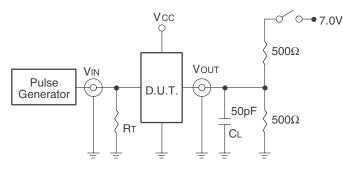
See test circuit and waveforms.
Minimum limits are guaranteed but not tested on Propagation Delays.

3. Skew between any two outputs, of the same package, switching in the same direction. This parameter is guaranteed by design.

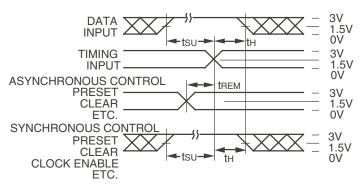
IDT54/74FCT162244T/AT/CT/ET FASTCMOS16-BITBUFFER/LINEDRIVER

MILITARY AND INDUSTRIAL TEMPERATURE RANGES

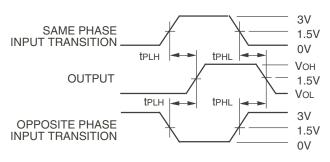
TEST CIRCUITS AND WAVEFORMS







Set-up, Hold, and Release Times



Propagation Delay

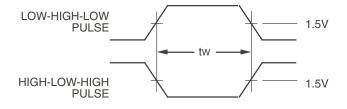
SWITCH POSITION

Test	Switch
Open Drain Disable Low Enable Low	Closed
All Other Tests	Open

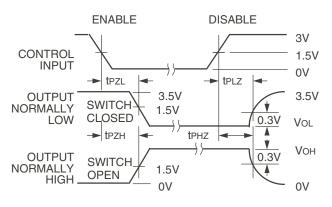
DEFINITIONS:

CL = Load capacitance: includes jig and probe capacitance.

RT = Termination resistance: should be equal to ZOUT of the Pulse Generator.



Pulse Width



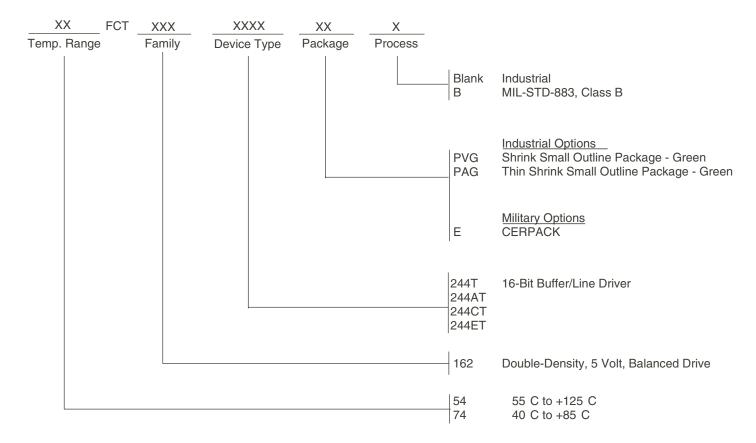


NOTES:

1. Diagram shown for input Control Enable-LOW and input Control Disable-HIGH.

2. Pulse Generator for All Pulses: Rate \leq 1.0MHz; tF \leq 2.5ns; tR \leq 2.5ns.

ORDERING INFORMATION



Datasheet Document History

09/06/09 Pg.6 Updated the ordering information by removing the "IDT" notation and non RoHS part.

IMPORTANT NOTICE AND DISCLAIMER

RENESAS ELECTRONICS CORPORATION AND ITS SUBSIDIARIES ("RENESAS") PROVIDES TECHNICAL SPECIFICATIONS AND RELIABILITY DATA (INCLUDING DATASHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS OR IMPLIED, INCLUDING, WITHOUT LIMITATION, ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE, OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for developers skilled in the art designing with Renesas products. You are solely responsible for (1) selecting the appropriate products for your application, (2) designing, validating, and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, or other requirements. These resources are subject to change without notice. Renesas grants you permission to use these resources only for development of an application that uses Renesas products. Other reproduction or use of these resources is strictly prohibited. No license is granted to any other Renesas intellectual property or to any third party intellectual property. Renesas disclaims responsibility for, and you will fully indemnify Renesas and its representatives against, any claims, damages, costs, losses, or liabilities arising out of your use of these resources. Renesas' products are provided only subject to Renesas' Terms and Conditions of Sale or other applicable terms agreed to in writing. No use o any Renesas resources expands or otherwise alters any applicable warranties or warranty disclaimers for these products.

(Disclaimer Rev.1.0 Mar 2020)

Corporate Headquarters

TOYOSU FORESIA, 3-2-24 Toyosu, Koto-ku, Tokyo 135-0061, Japan www.renesas.com

Trademarks

Renesas and the Renesas logo are trademarks of Renesas Electronics Corporation. All trademarks and registered trademarks are the property of their respective owners. **Contact Information**

For further information on a product, technology, the most up-to-date version of a document, or your nearest sales office, please visit: <u>www.renesas.com/contact/</u>